



HARRIS HI-5687V/883

Wide Temperature Range Monolithic 12-Bit Digital-to-Analog Converter

May 1988

Features

- This Circuit is Processed in Accordance with MIL-Std-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- DAC 87 Alternate Source
- Monolithic Construction (Single Chip)
- Fast Settling
- Guaranteed Specifications
- Wafer Laser Trimmed
- Applications Resistors On-Chip
- On-Chip Reference
- Dielectric Isolation (DI) Processing
- $\pm 12V$ Power Supply Operation

Applications

- High Speed A/D Converters
- Precision Instrumentation
- CRT Display Generation

Description

The HI-5687V/883 is a monolithic direct replacement for the popular DAC 87-CBI wide temperature range digital-to-analog converter. Single chip construction, along with several design innovations make the HI-5687/883 the optimum choice for low cost, high reliability applications.

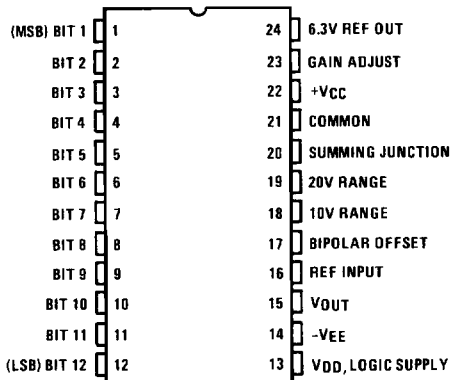
The Harris unique Dielectric Isolation (DI) processing reduces internal parasitics, resulting in fast switching times and minimum glitch. On-board span resistors are provided for good tracking over temperature, and are laser trimmed to high accuracy. These may be used with the on-chip op amp.

Internally, the HI-5687V/883 eliminates code dependent ground currents by routing current from the positive supply to the internal ground node, as determined by an auxiliary R-2R ladder. This results in a cancellation of code dependent ground currents, allowing virtually zero variation in current through the package common, pin 21, (25).

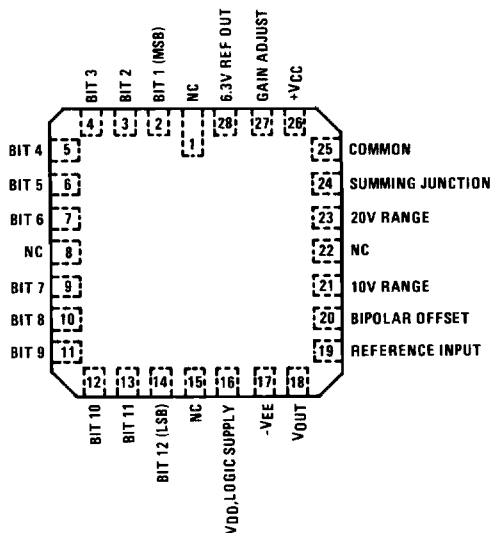
The HI-5687V/883 includes an on-chip output amplifier, a buried zener voltage reference featuring low temperature coefficient, and operates with a +5V logic supply and a +VCC, -VEE in the range of $\pm 11.4V$ to $\pm 16.5V$.

Pinouts

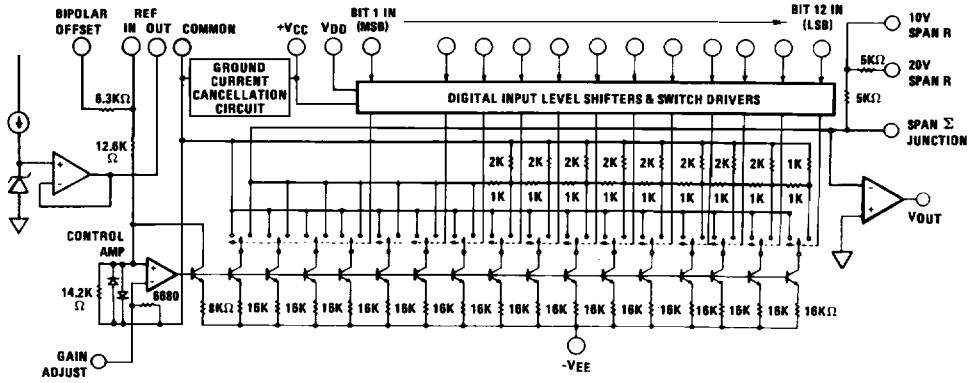
HI1-5687V/883 (CERAMIC SIDEBRAZE DIP)
TOP VIEW



HI4-5687V/883 (CERAMIC LCC)
TOP VIEW



Functional Block Diagram



6
DATA CONVERSION
PRODUCTS

Specifications HI-5687V/883

Absolute Maximum Ratings (Note 1)

All Voltages Referred to Common	
Power Supply Inputs	
+V _{CC}	+20V
-V _{EE}	-20V
V _{DD}	+20V
Reference	
Input	+V _{CC} to -V _{EE}
Output Current	6mA
Digital Inputs	
Bits 1 to 12	-1V to +12V
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering 10sec)	275°C
Junction Temperature	175°C

Thermal Information

Thermal Resistance, Junction-to-Case (θ_{JC})	
Ceramic DIP Package	12°C/W
Ceramic LCC Package	40°C/W
Thermal Resistance Junction-to-Ambient (θ_{JA})	
Ceramic DIP Package	49°C/W
Ceramic LCC Package	81°C/W
Power Dissipation at 75°C	
Ceramic DIP Package	2040mW
Ceramic LCC Package	1235mW
Power Dissipation Derating Factor (Above +75°C)	
Ceramic DIP Package	20.4mW/°C
Ceramic LCC Package	12.35mW/°C

Recommended Operating Conditions

Operating Temperature Range	-55°C to +125°C	Reference Input Voltage	6.3V
Operating Supply Voltage (Note 5);		Logic Low Level	0V to 0.8V
+V _{CC}	+12V to +15V	Logic High Level	2.0V to 5.5V
-V _{EE}	-12V to -15V		
+V _{DD}	+5V		

TABLE 1. D.C. ELECTRICAL PERFORMANCE CHARACTERISTICS

Devices Tested at +V_{CC} = +15V, -V_{EE} = -15V, V_{DD} = +5V, Reference Out Connected to Reference In, Pin numbers correspond to DIP package only; Unless Otherwise Specified.

D.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current From V _{CC}	I _{CC}	All Bits OFF, V _{IH} = 2.0V	1	+25°C	—	11.0	mA
			2, 3	-55°C, +125°C	—	13.5	mA
Supply Current From V _{EE}	I _{EE}	All Bits OFF, V _{IH} = 2.0V	1	+25°C	-20.0	—	mA
			2, 3	-55°C, +125°C	-22.5	—	mA
Supply Current From V _{DD}	I _{DD}	All Bits OFF, V _{IH} = 2.0V	1	+25°C	—	8.0	mA
			2, 3	-55°C, +125°C	—	9.50	mA
Digital Input Low Current	I _{IL}	Each Bit Tested Separately Input Under Test, V _{IL} = 0V, all other Bits, V _{IL} = 0.8V	1	+25°C	-50	—	μA
			2, 3	-55°C, +125°C	-100	—	μA
Digital Input High Current	I _{IH}	Each Bit Tested Separately Input Under Test, V _{IH} = 5.5V all other Bits, V _{IL} = 0.8V	1	+25°C	-0.25	0.25	μA
			2, 3	-55°C, +125°C	-1.0	1.0	μA
Reference Voltage Unipolar	V _{REF(U)}	All Bits OFF, V _{IH} = 2.0V Unipolar 10V Range	1	+25°C	6.20	6.40	V
			2, 3	-55°C, +125°C	6.20	6.40	V
Reference Voltage Bipolar Loaded	V _{REF(B)} V _{REF(L)}	Bipolar 20V Range Bipolar 20V Range 2.5mA Current Source from Pin 24 to Ground	1	+25°C	6.20	6.40	V
			2, 3	-55°C, +125°C	6.20	6.40	V
Unipolar Offset Error	V _{OS}	All Bits OFF, V _{IH} = 2.0V (Note 2)	1	+25°C	-0.10	0.10	% FSR
			2, 3	-55°C, +125°C	-0.13	0.13	% FSR
Unipolar Gain Error	A _E	All Bits OFF to all Bits ON V _{IH} = 2.0V, V _{IL} = 0.8V (Note 2)	1	+25°C	-0.20	0.20	% FSR
			2, 3	-55°C, +125°C	-0.45	0.45	% FSR
Unipolar Gain Error, ±5mA Load Current	A _{EI} ±	All Bits OFF to all Bits ON ±5mA Load Current from V _O (Pin 15) to Ground	1	+25°C	-0.20	0.20	% FSR
			2, 3	-55°C, +125°C	-0.45	0.45	% FSR
Power Supply Sensitivity From V _{CC}	+P _{SS1}	All Bits ON, V _{IL} = 0.8V V _{CC} from 16.5V to 11.4V Bipolar Mode, ±5V Range	1	+25°C	-0.002	0.002	$\frac{\Delta}{\%}$ FSR % Δ V _{CC}
Power Supply Sensitivity From V _{DD}	+P _{SS2}	All Bits ON, V _{IL} = 0.8V V _{DD} from 4.5V to 5.5V Bipolar Mode ±5V Range	1	+25°C	-0.002	0.002	$\frac{\Delta}{\%}$ FSR % Δ V _{DD}
Power Supply Sensitivity From V _{EE}	-P _{SS1}	All Bits ON, V _{IN} = 0.8V V _{EE} from -16.5V to -11.4V Bipolar Mode ±5V Range	1	+25°C	-0.002	0.002	$\frac{\Delta}{\%}$ FSR % Δ V _{EE}

CAUTION: These devices are sensitive to electrostatic discharge. Proper IC handling procedures should be followed.

Specifications HI-5687V/883

TABLE 1. D.C. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Devices Tested at $+V_{CC} = +15V$, $-V_{EE} = -15V$, $V_{DD} = +5V$, Reference Out connected to Reference In, Pin numbers correspond to DIP package only, Unless Otherwise Specified.

D.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Bipolar Offset Error	BPOE	All Bits OFF, $V_{IH} = 2.0V$ Bipolar $\pm 10V$ Range (Note 2)	1	+25°C	-0.10	0.10	% FSR
			2, 3	-55°C, +125°C	-0.20	0.20	% FSR
Bipolar Zero Error	BPZE	MSB ON, $V_{IL} = 0.8V$; all other Bits OFF. $V_{IH} = 2.0V$ Bipolar $\pm 10V$ Range	1	+25°C	-0.10	0.10	% FSR
			2, 3	-55°C, +125°C	-0.20	0.20	% FSR
Bipolar Gain Error	BPAE	All Bits OFF, to all Bits ON, $V_{IH} = 2V$. $V_{IL} = 0.8V$ Bipolar $\pm 10V$ Range (Note 2)	1	+25°C	-0.20	0.20	% FSR
			2, 3	-55°C, +125°C	-0.45	0.45	% FSR
Integral Linearity Error	LE	Unipolar Mode 10V Range, Reference Chart B for Codes Tested	1	+25°C	-0.375	0.375	LSB
			2, 3	-55°C, +125°C	-0.75	0.75	LSB
Differential Linearity Error	DLE	Unipolar Mode 10V Range Reference Chart C for Codes Tested	1	+25°C	-0.50	0.50	LSB
			2, 3	-55°C, +125°C	-1.0	1.0	LSB
Gain Adjust	AA	Unipolar Mode All Bits ON, $V_{IL} = 0.8V$ (Note 6)	1	+25°C	± 0.20	—	% FSR
Reference Voltage Drift Unipolar	$\frac{dV_{REF(U)}}{dT}$	(Note 3)	1, 2	+25°C, +125°C	-20	20	ppm of V_{REF}
			1, 3	+25°C, -55°C	-20	20	°C
Reference Voltage Drift Bipolar	$\frac{dV_{REF(B)}}{dT}$	(Note 3)	1, 2	+25°C, +125°C	-20	20	ppm of V_{REF}
			1, 3	+25°C, -55°C	-20	20	°C
Unipolar Offset Drift	$\frac{dV_{OS}}{dT}$	(Note 3)	1, 2	+25°C, +125°C	+3.0	-3.0	ppm of FSR
			1, 3	+25°C, -55°C	+3.0	-3.0	°C
Unipolar Gain Drift	$\frac{dA_{E1}}{dT}$	(Note 3)	1, 2	+25°C, +125°C	-25	+25	ppm of FSR
			1, 3	+25°C, -55°C	-25	+25	°C
Unipolar Gain Drift Exclusive of the Internal Reference	$\frac{dA_{E2}}{dT}$	(Note 3)	1, 2	+25°C, +125°C	-10	+10	ppm of FSR
			1, 3	+25°C, -55°C	-10	+10	°C
Total Unipolar Error	UET	(Note 3)	1, 2	+25°C, +125°C	-0.3	0.3	% FSR
			1, 3	+25°C, -55°C	-0.3	0.3	% FSR
Bipolar Offset Drift	$\frac{dBPOE}{dT}$	(Note 3)	1, 2	+25°C, +125°C	-10	+10	ppm of FSR
			1, 3	+25°C, -55°C	-10	+10	°C
Bipolar Gain Drift	$\frac{dBPAE1}{dT}$	(Note 3)	1, 2	+25°C, +125°C	-25	25	ppm of FSR
			1, 3	+25°C, -55°C	-25	25	°C
Bipolar Gain Drift Exclusive of the Internal Reference	$\frac{dBPAE2}{dT}$	(Note 3)	1, 2	+25°C, +125°C	-10	10	ppm of FSR
			1, 3	+25°C, -55°C	-10	10	°C
Total Bipolar Error	BET	(Note 3)	1, 2	+25°C, +125°C	-0.24	0.24	% FSR
			1, 3	+25°C, -55°C	-0.24	0.24	% FSR
Total Bipolar Drift	$\frac{dBPT}{dT}$	(Note 3)	1, 2	+25°C, +125°C	-30	30	ppm of FSR
			1, 3	+25°C, -55°C	-30	30	°C

- NOTES: 1. Absolute maximum ratings are limiting values, applied individually, beyond which the serviceability of the circuit may be impaired. Functional operation under any of these conditions is not necessarily implied.
2. Adjustable to zero using external potentiometers.
3. See Definitions.
4. FSR is a "Full Scale Range" and is 20V for $\pm 10V$ range, 10V for $\pm 5V$ range, etc.
5. The HI-5687/883 will operate with supply voltage as low as $\pm 11.4V$. It is recommended that output voltage ranges -10V to +10V not be used if the supply voltages are less than $\pm 12.5V$.
6. Gain Adjust capability is tested by first measuring the full scale output voltage with pin 23 (DIP package) open, positive and negative adjustability are checked by applying $\pm 15V$ to pin 23 (DIP package) through a 2.8M Ω resistor and measuring the full scale voltage for each condition. A minimum delta of $\pm 20mV$ with respect to the initial reading guarantees ideal full scale adjustment as the gain error specification at +25°C is $\pm 20mV$ (0.2% FSR).

Specifications HI-5687V/883

TABLE 2. A.C. ELECTRICAL PERFORMANCE CHARACTERISTICS

Devices Tested at $+V_{CC} = +15V$, $-V_{EE} = -15V$, $V_{DD} = +5V$, Reference Out Connected to Reference In, Unless Otherwise Specified

A.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMP	LIMITS		UNITS
					MIN	MAX	
Positive Slew Rate	S_{R+}	All Bits OFF ($V_{IH} = 2V$) to all Bits ON ($V_{IL} = 0.8V$). Bipolar $\pm 10V$ Range. Measurement Points at $-6V$ and $+6V$. Figure 2.	4	$+25^{\circ}C$	11.0	—	$V/\mu s$
Negative Slew Rate	S_{R-}	All Bits ON ($V_{IL} = 0.8V$) to all Bits OFF ($V_{IH} = 2.0V$). Bipolar $\pm 10V$ Range. Measurement Points at $+6V$ and $-6V$. Figure 2.	4	$+25^{\circ}C$	11.0	—	$V/\mu s$

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Characterized at $+V_{CC} = +15V$, $-V_{EE} = -15V$, $V_{DD} = +5V$, Reference Out Connected to Reference In, Unless Otherwise Specified

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMP	LIMITS		UNITS
					MIN	MAX	
Settling Time	t_S	To $\pm 0.5LSB$ for Full Scale Transition Unipolar 10V Range. $R_L = 5k\Omega$ Figures 3 & 4	3, 7	$+25^{\circ}C$	—	2.0	μs

NOTES: 7. The parameters listed in Table 3 are controlled via design or process parameters and are not directly tested. These parameters are characterized upon initial design release and upon design changes which would affect these characteristics.

TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLES 1, 2 & 3)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1*, 2, 3, 4
Group A Test Requirements	1, 2, 3, 4
Groups C & D Endpoints	1

*PDA applies to Subgroup 1 only. No other subgroups are included in PDA.

Test Circuit & Test Conditions

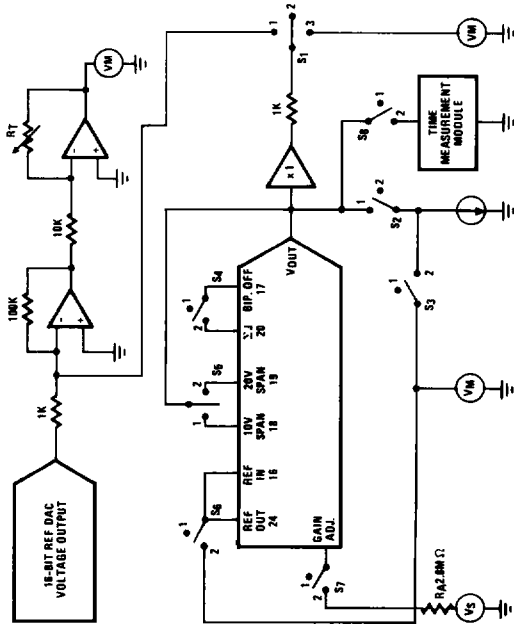


FIGURE 1. TEST CIRCUIT

CHART A. GROUP A TEST CONDITIONS

Pin 24 Tied to Pin 16, and Pin 23 Open Unless Otherwise Noted, All Pin Number's Listed Refer to the 24 Lead DIP Package.

TEST	SYMBOL	CONDITIONS	PIN13 VDD	PIN14 VEE	PIN15 VOUT	PIN17 B.P. ROUT	PIN18 10V SPAN	PIN19 20V SPAN	PIN20 ΣJ	PIN22 YCC	SWITCH POSITION								MEASURE	
											S1	S2	S3	S4	S5	S6	S7	S8	VALUE	UNIT
Supply Current From V _{CC}	I _{CC}	All Bits OFF, V _{IH} = 2.0V	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	2	2	1	1	1	1	1	1	—	mA
Supply Current From V _{EE}	I _{EE}	All Bits OFF, V _{IH} = 2.0V	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	2	2	1	1	1	1	1	1	—	mA
Supply Current From V _{DD}	I _{DD}	All Bits OFF, V _{IH} = 2.0V	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	2	2	1	1	1	1	1	1	—	mA
Digital Input Low Current	I _{IL}	Each Bit Test Separately Bit Input Under Test. V _{IH} = 0V, All Other Bits, V _{IL} = 0.8V	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	2	2	1	1	1	1	1	1	—	µA
Digital Input High Current	I _{IH}	Each Bit Test Separately Bit Input Under Test. V _{IH} = 5.5V, All Other Bits, V _{IL} = 0.8V	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	2	2	1	1	1	1	1	1	—	µA

DATA CONVERSION PRODUCTS

Test Conditions

CHART A. GROUP A TEST CONDITIONS (Continued)

Pin 24 Tied to Pin 16, and Pin 23 Open Unless Otherwise Noted. All Pin Number's Listed Refer to the 24 Lead DIP Package.

TEST	SYMBOL	CONDITIONS	PIN13	PIN14	PIN15	PIN17	PIN18	PIN19	PIN20	PIN22	SWITCH POSITION								MEASURE		EQUATIONS						
											VDD	VEE	ROUT	B.P.	10V SPAN	20V SPAN	ΣI	VCC	S1	S2		S3	S4	S5	S6	S7	S8
Reference Voltage Loaded	VREF(L)	All Bits OFF (V _{IH} = 2V) 2.5mA Current Source From Pin 24 to GND. Bipolar Mode ±10V Range	5V	-15V	Pin 19	Pin 20	O.C.	Pin 15	Pin 17	15V	2	2	2	2	2	2	2	1	1	1	1	1	1	1	E1R E1H E1L	V	
Reference Voltage Unipolar Mode	VREF(U)	All Bits OFF (V _{IH} = 2V)	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	2	2	1	1	1	1	1	1	1	1	1	1	1	1	E2R E2H E2L	V	
Reference Voltage Bipolar Mode	VREF(B)	All Bits OFF (V _{IH} = 2V) Bipolar Mode ±10V Range	5V	-15V	Pin 19	Pin 20	O.C.	Pin 15	Pin 17	15V	2	2	1	2	2	2	1	1	1	1	1	1	1	1	E3R E3H E3L	V	
Unipolar Offset	VOS	All Bits OFF (V _{IH} = 2V)	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	3	2	1	1	1	1	1	1	1	1	1	1	1	1	E4R E4H E4L	V	$\frac{E4 \times 100}{10} = \% \text{FSR}$
Unipolar Gain Error	AE1	All Bits OFF to All Bits ON. (V _{IH} = 2V, V _{IL} = 0.8V)	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	3	2	1	1	1	1	1	1	1	1	1	1	1	1	E5R E5H E5L	V	$\frac{ E5 \cdot E4 \cdot 9.99756}{10} \times 100 = \% \text{FSR}$
Unipolar Gain Error Output Loaded	AE2	All Bits OFF to All Bits ON. (V _{IH} = 2V, V _{IL} = 0.8V) *5mA Current Source From V _{OUT} to GND	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	3	1	1	1	1	1	1	1	1	1	1	1	1	1	E6R E6H E6L	V	Calculation Same as Above
Unipolar Gain Error Output Loaded	AE3	All Bits OFF to All Bits ON. V _{IL} = 0.8V *5mA Current Source From V _{OUT} to GND	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	3	1	1	1	1	1	1	1	1	1	1	1	1	1	E7R E7H E7L	V	Calculation Same as Above
Power Supply Sensitivity From VCC	+PSS1	All Bits ON; V _{IL} = 0.8V VCC = 16.5/11.4V Bipolar ±5V Range	5V	-15V	Pin 18	Pin 20	Pin 15	O.C.	Pin 17	16.5V 11.4V	3	2	1	2	1	1	1	1	1	1	1	1	1	1	E8A E8B	V	$\frac{E8A - E8B}{(10)(34\%)} \times 100 = \% \Delta \text{VCC}$
Power Supply Sensitivity From VDD	+PSS2	All Bits ON; V _{IL} = 0.8V VDD = 5.5V/4.5V Bipolar ±5V Range	5.5V 4.5V	-15V	Pin 18	Pin 20	Pin 15	O.C.	Pin 17	15V	3	2	1	2	1	1	1	1	1	1	1	1	1	1	E9A E9B	V	$\frac{E9A - E9B}{(10)(34\%)} \times 100 = \% \Delta \text{VCC}$
Power Supply Sensitivity From VEE	-PSS1	All Bits ON; V _{IL} = 0.8V VEE = -16.5/-11.4V Bipolar ±5V Range	5V	-16.5V -11.4V	Pin 18	Pin 20	Pin 15	O.C.	Pin 17	15V	3	2	1	2	1	1	1	1	1	1	1	1	1	1	E10A E10B	V	$\frac{E10A - E10B}{(10)(34\%)} \times 100 = \% \Delta \text{VEE}$
Bipolar Offset Error	BPOE	All Bits OFF; V _{IH} = 2V ±10V Range	5V	-15V	Pin 19	Pin 20	O.C.	Pin 15	Pin 17	15V	3	2	1	2	2	1	1	1	1	1	1	1	1	1	E11R E11H E11L	V	$\frac{E11 \times 10}{20} \times 100 = \% \text{FSR}$

Test Conditions

CHART A. GROUP A TEST CONDITIONS (Continued)

Pin 24 Tied to Pin 16, and Pin 23 Open Unless Otherwise Noted. All Pin Number's Listed Refer to the 24 Lead DIP Package.

TEST	SYMBOL	CONDITIONS	SWITCH POSITION										MEASURE		EQUATIONS						
			PIN13	PIN14	PIN15	PIN17	PIN18	PIN19	PIN20	PIN22	S ₁	S ₂	S ₃	S ₄		S ₅	S ₆	S ₇	S ₈	VALUE	UNIT
Bipolar Zero Error	BPZE	MSB ON, V _{IL} = 0.8V All Other Bits OFF, V _{IH} = 2.0V, ±10V Range	V _{DD}	V _{EE}	V _{OUT}	B.P. ROUT	10V SPAN	20V SPAN	Σ _J	V _{CC}	S ₁	S ₂	S ₃	S ₄	S ₅	S ₆	S ₇	S ₈	E _{12R} E _{12H} E _{12L}	V	$\frac{E_{12} \times 100 = \%FSR}{20}$
Bipolar Gain Error	BPAE	All Bits OFF (V _{IH} = 2V) to All Bits ON (V _{IL} = 0.8V) ±10V Range	5V	-15V	Pin 19	Pin 20	O.C.	Pin 15	Pin 17	15V	3	2	1	2	2	1	1	1	E _{13R} E _{13H} E _{13L}	V	$\left[\frac{(E_{13}-E_{11})-19.995}{20} \right] \times 100 = \%FSR$
Integral Linearity Error	LE	Unipolar Mode, 0 to 10V Range V _{IL} = 0.8V, V _{IH} = 2.0V	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	1	2	1	1	1	1	1	1	ELR ELH ELL	V	$E_L(1LSB) = LSBs\ of\ Error$
Differential Linearity Error	DLE	Unipolar Mode 0 to 10V Range V _{IL} = 0.8V, V _{IH} = 2.0V	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	1	2	1	1	1	1	1	1	EDLR EDLH EDLL	V	$EDL(1LSB) = LSBs\ of\ Error$
Gain Adjust	AA	V _S = -15V, R _A = 2.8MΩ V _S = -15V, R _A = 2.8MΩ	5V	-15V	Pin 18	O.C.	Pin 15	O.C.	O.C.	15V	3	2	1	1	1	1	2	1	E ₁₄ E ₁₅	V	$\frac{E_{14}-E_{6R} \times 100 = \%FSR}{10}$ $\frac{E_{6R}-E_{15} \times 100 = \%FSR}{10}$
Positive Slew Rate	+SR	All Bits OFF (V _{IH} = 2V) to All Bits ON (V _{IL} = 0.8V) Bipolar ±10V Range	5V	-15V	Pin 19	Pin 20	O.C.	Pin 15	Pin 17	15V	2	2	1	2	2	1	1	2	T ₁ T ₂	μs	$\frac{12V}{T_2-T_1} = \frac{V}{\mu s}$
Negative Slew Rate	-SR	All Bits ON (V _{IL} = 0.8V) to All Bits OFF (V _{IH} = 2V) Bipolar ±10V Range	5V	-15V	Pin 19	Pin 20	O.C.	Pin 15	Pin 17	15V	2	2	1	2	2	1	1	2	T ₃ T ₄	μs	$\frac{12V}{T_3-T_4} = \frac{V}{\mu s}$

TEST	SYMBOL	CONDITIONS	TEMPERATURE	EQUATIONS
Reference Voltage Drift Unipolar Mode	$\frac{dV_{REF}(U)}{dT}$	Calculations Made From Tests Previously Defined in this Chart	+25°C to +125°C	$\frac{(E_{2H}-E_{2R})10^6}{E_{2R}(100^\circ C)} = \frac{PPM\ of\ V_{REF}}{^\circ C}$
Reference Voltage Drift Bipolar Mode	$\frac{dV_{REF}(B)}{dT}$	Calculations Made From Tests Previously Defined in this Chart	-55°C to +25°C	$\frac{(E_{2R}-E_{2L})10^6}{E_{2R}(80^\circ C)} = \frac{PPM\ of\ V_{REF}}{^\circ C}$
Unipolar Offset Drift	$\frac{dV_{OS}}{dT}$	Calculations Made From Tests Previously Defined in this Chart	+25°C to +125°C	$\frac{(E_{3H}-E_{3L})10^6}{E_{3R}(100^\circ C)} = \frac{PPM\ of\ V_{REF}}{^\circ C}$
			-55°C to +25°C	$\frac{(E_{3R}-E_{3L})10^6}{E_{3R}(80^\circ C)} = \frac{PPM\ of\ V_{REF}}{^\circ C}$
			+25°C to +125°C	$\frac{(E_{4H}-E_{4R})10^6}{10(100^\circ C)} = \frac{PPM\ of\ FSR}{^\circ C}$
			-55°C to +25°C	$\frac{(E_{4R}-E_{4L})10^6}{10(80^\circ C)} = \frac{PPM\ of\ FSR}{^\circ C}$

Test Conditions

CHART A. GROUP A TEST CONDITIONS (Continued)

Pin 24 Tied to Pin 16, and Pin 23 Open Unless Otherwise Noted. All Pin Number's Listed Refer to the 24 Lead DIP Package.

TEST	SYMBOL	CONDITIONS	TEMPERATURE	EQUATIONS
Unipolar Gain Drift	$\frac{dA_{E1}}{dT}$	Calculations Made From Tests Previously Defined in This Chart	+25°C to +125°C	$\left[\frac{(E_{5H}-E_{4H}) - (E_{5R}-E_{4R})}{10 (100^\circ\text{C})} \right] 10^6 = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
			-55°C to +25°C	$\left[\frac{(E_{5R}-E_{4R}) - (E_{5L}-E_{4L})}{10 (80^\circ\text{C})} \right] 10^6 = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
Unipolar Gain Drift Exclusive of the Internal Reference	$\frac{dA_{E2}}{dT}$	Calculations Made From Tests Previously Defined in This Chart	+25°C to +125°C	$\left[\frac{(E_{5H}-E_{4H}) - (E_{5R}-E_{4R}) - (E_{2H}-E_{2R})}{10} \right] \cdot \frac{10^6}{6.3} = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
			-55°C to +25°C	$\left[\frac{(E_{5R}-E_{4R}) - (E_{5L}-E_{4L}) - (E_{2R}-E_{2L})}{10} \right] \cdot \frac{10^6}{6.3} = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
Total Unipolar Error	UET	Calculations Made From Tests Previously Defined in This Chart	+25°C to +125°C	$\frac{(E_{5H}-E_{5R})}{10} (100) = \% \text{FSR}$
Bipolar Offset Drift	$\frac{dB_{OE}}{dT}$	Calculations Made From Tests Previously Defined in This Chart	+25°C to +125°C	$\frac{(E_{11H}-E_{11R})}{20 (100^\circ\text{C})} 10^6 = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
			-55°C to +25°C	$\frac{(E_{11R}-E_{11L})}{20 (80^\circ\text{C})} 10^6 = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
Bipolar Gain Drift	$\frac{dB_{PAE1}}{dT}$	Calculations Made From Tests Previously Defined in This Chart	+25°C to +125°C	$\left[\frac{(E_{13H}-E_{11H}) - (E_{13R}-E_{11R})}{20 (100^\circ\text{C})} \right] 10^6 = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
			-55°C to +25°C	$\left[\frac{(E_{13R}-E_{11R}) - (E_{13L}-E_{11L})}{20 (80^\circ\text{C})} \right] 10^6 = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
Bipolar Gain Drift Exclusive of the Internal Reference	$\frac{dB_{AE2}}{dT}$	Calculations Made From Tests Previously Defined in This Chart	+25°C to +125°C	$\left[\frac{(E_{13H}-E_{11H}) - (E_{13R}-E_{11R}) - (E_{3H}-E_{3R})}{20} \right] \cdot \frac{10^6}{6.3} = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
			-55°C to +25°C	$\left[\frac{(E_{13R}-E_{11R}) - (E_{13L}-E_{11L}) - (E_{3R}-E_{3L})}{20} \right] \cdot \frac{10^6}{6.3} = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
Total Bipolar Error	BET	Calculations Made From Tests Previously Defined in This Chart	+25°C to +125°C	$\frac{(E_{13H} - E_{13R})}{20} (100) = \% \text{FSR}$
Total Bipolar Drift	$\frac{dBp}{dT}$	Calculations Made From Tests Previously Defined in This Chart	+25°C to +125°C	$\frac{(E_{13R} - E_{13L})}{20} (100) = \% \text{FSR}$
			-55°C to +25°C	$\frac{(E_{13H} - E_{13R})}{20 (100^\circ\text{C})} 10^6 = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
Total Bipolar Drift	$\frac{dBp}{dT}$	Includes Gain, Offset and Linearity Drift	+25°C to +125°C	$\frac{(E_{13R} - E_{13L})}{20 (80^\circ\text{C})} 10^6 = \frac{\text{PPM of FSR}}{^\circ\text{C}}$
			-55°C to +25°C	$\frac{(E_{13R} - E_{13L})}{20 (80^\circ\text{C})} 10^6 = \frac{\text{PPM of FSR}}{^\circ\text{C}}$

Waveforms

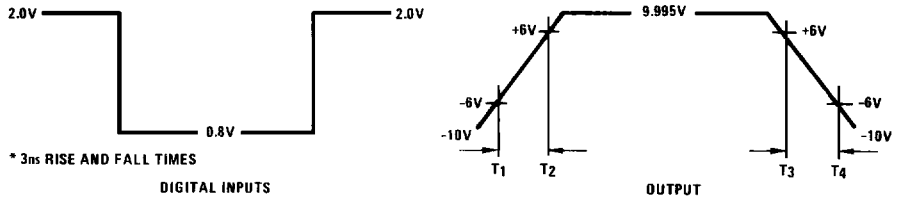


FIGURE 2. SLEW RATE WAVEFORMS

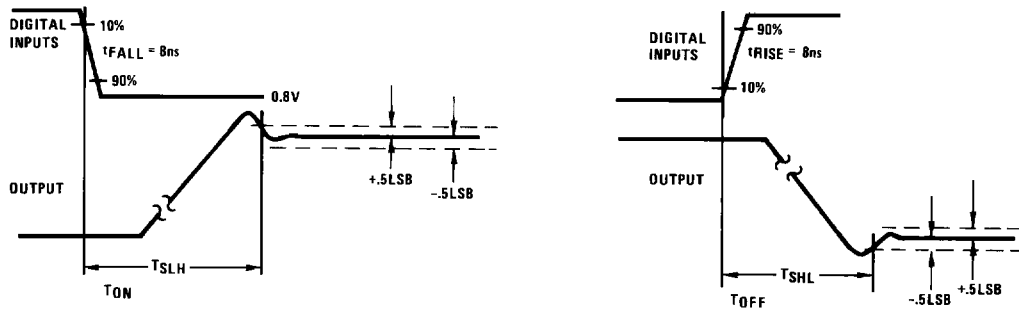


FIGURE 3. SETTLING TIME WAVEFORMS

Test Circuit

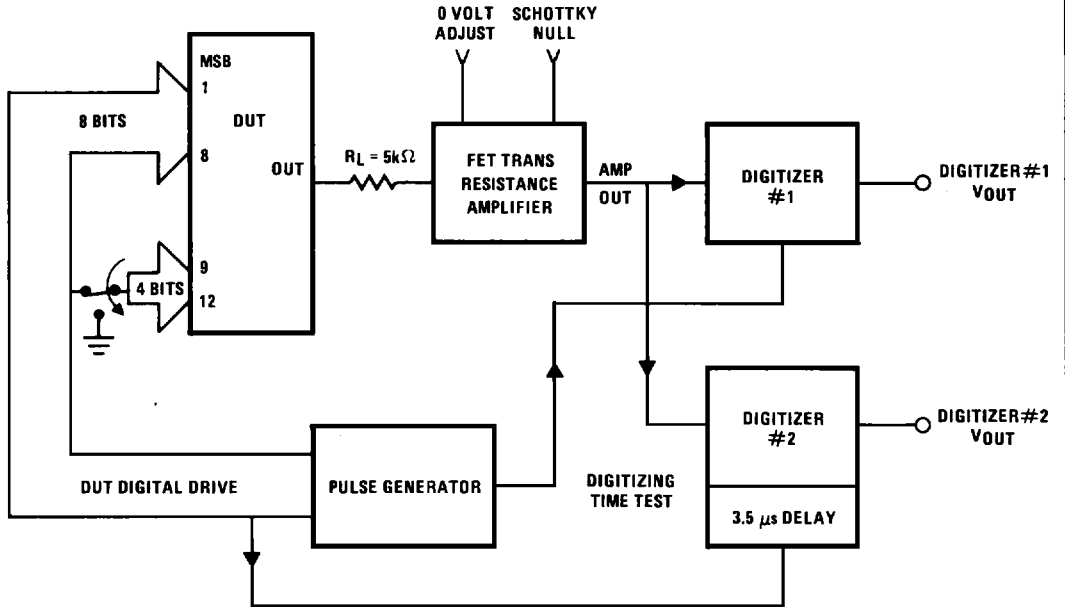


FIGURE 4. SETTLING TIME TEST FIXTURE

CHART B.

DIGITAL CODE		NOTE	DIGITAL CODE		NOTE
MSB	LSB		MSB	LSB	
1 1 1 1 1 1 1 1 1 1 1 0			1 0 0 1 X X X X X X X X	9	
1 1 1 1 1 1 1 1 1 1 0 1			1 0 0 0 X X X X X X X X	8	
1 1 1 1 1 1 1 1 1 0 1 1			1 0 0 0 X X X X X X X X	9	
1 1 1 1 1 1 1 1 1 0 1 1			0 1 1 1 X X X X X X X X	8	
1 1 1 1 1 1 1 1 0 1 1 1			0 1 1 1 X X X X X X X X	9	
1 1 1 1 1 1 1 0 1 1 1 1			0 1 1 0 X X X X X X X X	8	
1 1 1 1 1 1 0 1 1 1 1 1			0 1 1 0 X X X X X X X X	9	
1 1 1 1 0 1 1 1 1 1 1 1			0 1 0 1 X X X X X X X X	8	
1 1 1 0 1 1 1 1 1 1 1 1			0 1 0 1 X X X X X X X X	9	
1 1 0 1 1 1 1 1 1 1 1 1			0 1 0 0 X X X X X X X X	8	
1 0 1 1 1 1 1 1 1 1 1 1			0 1 0 0 X X X X X X X X	9	
0 1 1 1 1 1 1 1 1 1 1 1			0 0 1 1 X X X X X X X X	8	
1 1 1 0 X X X X X X X X	8		0 0 1 1 X X X X X X X X	9	
1 1 1 0 X X X X X X X X	9		0 0 1 0 X X X X X X X X	8	
1 1 0 1 X X X X X X X X	8		0 0 1 0 X X X X X X X X	9	
1 1 0 1 X X X X X X X X	9		0 0 0 1 X X X X X X X X	8	
1 1 0 0 X X X X X X X X	8		0 0 0 1 X X X X X X X X	9	
1 1 0 0 X X X X X X X X	9		0 0 0 0 X X X X X X X X	8	
1 0 1 1 X X X X X X X X	8		0 0 0 0 X X X X X X X X	9	
1 0 1 1 X X X X X X X X	9		X X X X X X X X X X X X	8	
1 0 1 0 X X X X X X X X	8		X X X X X X X X X X X X	9	
1 0 1 0 X X X X X X X X	9				
1 0 0 1 X X X X X X X X	8				

NOTES: 8. X = 0 (V_{IL} = 0.8V) if the linearity error for that bit was measured as a positive error. X = 1 (V_{IH} = 2.0V) if the linearity error for that bit was measured as a negative error.
 9. X = 0 (V_{IL} = 0.8V) if the linearity error for that bit was measured as a negative error. X = 1 (V_{IH} = 2.0V) if the linearity error for that bit was measured as a positive error.

Integral Linearity Error Measurements

The transfer characteristics of the DUT are first determined by measuring its end points (all bits OFF, all bits ON). The end points of the reference DAC are then matched to the DUTs through software and hardware adjustments, to establish an ideal transfer characteristic for the DUT. The reference DAC then supplies one 12-bit LSB (DUT, all Bits OFF) to the input of the error amplifier and R_T is adjusted to obtain an output of 1V. The integral

linearity error, measured at the output of the error amplifier is the difference between the ideal voltage supplied by the reference DAC and the output voltage of the DUT for the code under test

$$\text{LSB's of Error} = \frac{(\text{Ideal voltage} - \text{measured voltage}) \times \text{LSB's}}{\text{Volt}}$$

6
DATA CONVERSION PRODUCTS

CHART C.

TO CODE										FROM CODE									
MSB					LSB					MSB					LSB				
1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
1	1	1	1	1	1	1	1	1	1	0	1	1	1	1	1	1	1	1	1
1	1	1	1	1	1	1	1	1	0	1	1	1	1	1	1	1	1	1	0
1	1	1	1	1	1	1	1	0	1	1	1	1	1	1	1	1	1	1	0
1	1	1	1	1	1	1	1	0	1	1	1	1	1	1	1	1	1	1	0
1	1	1	1	1	1	0	1	1	1	1	1	1	1	1	1	1	1	1	0
1	1	1	1	1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	1	1	1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	1	1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	1	1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	1	0	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
1	0	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
0	1	1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
0	1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
0	1	0	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
0	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
0	0	1	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
0	0	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0
0	0	0	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0

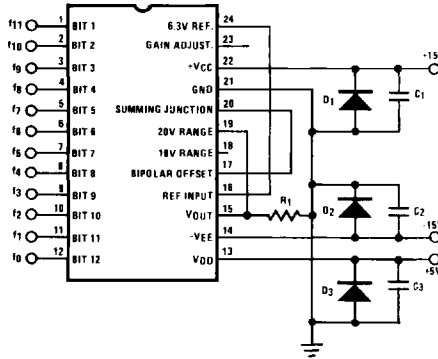
Differential Linearity Error Measurements

The DUT and the reference DAC supply the code under test to the input of the error amplifier, and the resulting output error is measured (E_1). The digital code of the DUT

is then increased by 1LSB and the output error is measured a second time (E_2). The differential linearity error is calculated as, $\frac{(E_2 - E_1)}{\text{Volts/LSB}} - 1\text{LSB} = \text{LSB's of error.}$

Burn-In Circuits

HI-5687V/883 (CERAMIC SIDEBRAZE DIP)

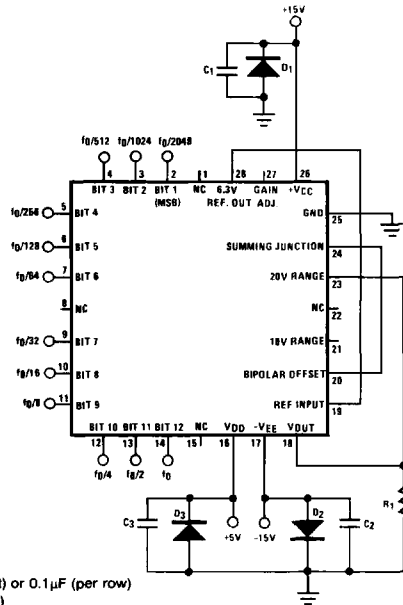


NOTES:

$R_1 = 2.0k\Omega, \pm 5\%$, 1/2 or 1/4 Watt
 $C_1 - C_3 = 0.01\mu F$ (one each per socket) or $0.1\mu F$ (per row)
 $D_1 - D_3 = 1N4003$ (one each per board)

$f_0 = 100kHz$	TTL Logic Levels	$f_6 = f_0/64$	TTL Logic Levels
$f_1 = f_0/2$	50% Duty Cycle	$f_7 = f_0/128$	50% Duty Cycle
$f_2 = f_0/4$		$f_8 = f_0/256$	
$f_3 = f_0/8$		$f_9 = f_0/512$	
$f_4 = f_0/16$		$f_{10} = f_0/1024$	
$f_5 = f_0/32$		$f_{11} = f_0/2048$	

HI-5687V/883 (CERAMIC LCC)



NOTES:

$R_1 = 2.0k\Omega, \pm 5\%$, 1/2 or 1/4 Watt
 $C_1 - C_3 = 0.01\mu F$ (one each per socket) or $0.1\mu F$ (per row)
 $D_1 - D_3 = 1N4002$ (one each per board)
 $f_0 = 100kHz$ (TTL Logic Level), 50% Duty Cycle

6
DATA CONVERSION PRODUCTS

Die Characteristics

DIE DIMENSIONS: 125 x 210 x 19 mils

METALLIZATION:

Type: Al

Thickness: $16k\text{\AA} \pm 2k\text{\AA}$

GLASSIVATION:

Type: Silox

Thickness: $14k\text{\AA} \pm 2.0k\text{\AA}$

WORST CASE CURRENT DENSITY: $2.26 \times 10^5 \text{A/cm}^2$

This device meets Glassivation Integrity Test requirement per Mil-Std-883 Method 2021 and Mil-M-38510 paragraph 3.5.5.4.

TRANSISTOR COUNT: 259

PROCESS: Bipolar-DI

DIE ATTACH:

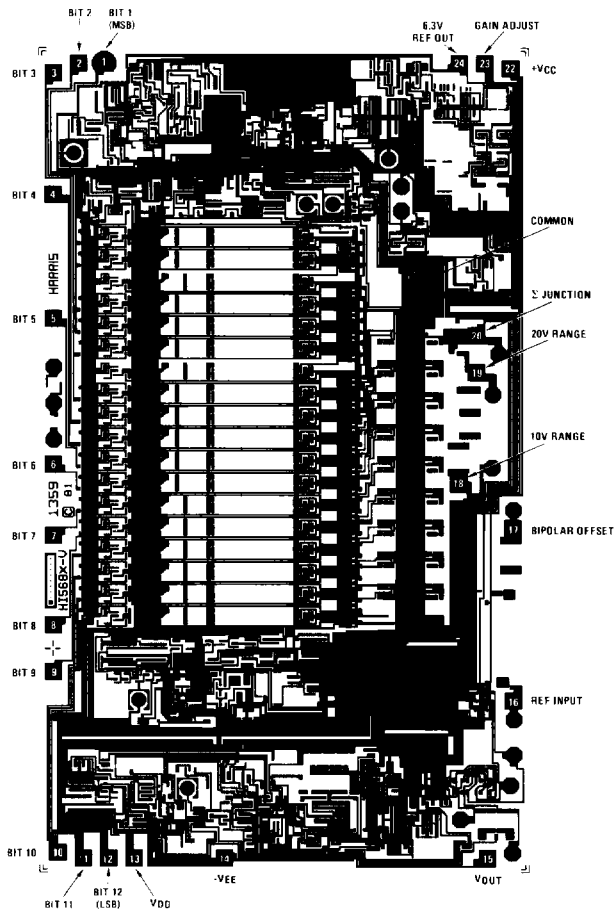
Material: Gold/Silicon Eutectic Alloy

Temperature: Ceramic DIP - 460°C (Max)

Ceramic LCC - 420°C (Max)

Metallization Mask Layout

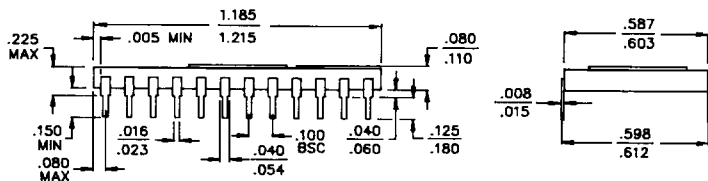
HI-5687V/883



NOTE: Pad Numbers Correspond to DIP Package Only.

Packaging †

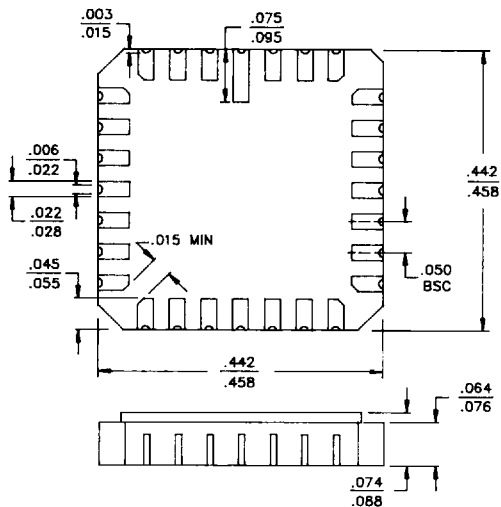
24 PIN CERAMIC SIDEBRAZE DIP



LEAD MATERIAL: Type B
LEAD FINISH: Type C
PACKAGE MATERIAL: Multilayer Ceramic, 90% Alumina
PACKAGE SEAL:
 Material: Gold/Tin (80/20)
 Temperature: 450°C ± 10°C
 Method: Furnace Seal

INTERNAL LEAD WIRE:
 Material: Aluminum
 Diameter: 1.25 Mil
 Bonding Method: Ultrasonic
COMPLIANT OUTLINE: 38510 D-3

28 PAD CERAMIC LCC



PAD MATERIAL: Type C
PAD FINISH: Type A
FINISH DIMENSION: Type A
PACKAGE MATERIAL: Multilayer Ceramic, 90% Alumina
PACKAGE SEAL:
 Material: Gold/Tin (80/20)
 Temperature: 320°C ± 10°C
 Method: Furnace Braze

INTERNAL LEAD WIRE:
 Material: Aluminum
 Diameter: 1.25 Mil
 Bonding Method: Ultrasonic
COMPLIANT OUTLINE: 38510 C-4

6
DATA CONVERSION
PRODUCTS

NOTE: All Dimensions are $\frac{\text{Min}}{\text{Max}}$ Dimensions are in inches.

† Mil-M-38510 Compliant Materials, Finishes, and Dimensions.

DESIGN INFORMATION

Wide Temperature Range Monolithic 12-Bit Digital-to-Analog Converter

The information contained in this section has been developed through characterization by Harris Semiconductor and is for use as application and design data only. No guarantee is implied.

Definitions of Specifications

Digital Inputs

The HI-5687V accepts digital input codes in complementary binary, complementary offset binary, and complementary two's complement binary.

DIGITAL INPUT	ANALOG OUTPUT		
	COMPLEMENTARY BINARY	COMPLEMENTARY OFFSET BINARY	COMPLEMENTARY TWO'S COMPLEMENT*
MSB LSB			
000 ... 000	+Full Scale	+Full Scale	-LSB
100 ... 000	Mid Scale -1 LSB	-1 LSB	+Full Scale
111 ... 111	Zero	-Full Scale	Zero
011 ... 111	+1/2 Full Scale	Zero	-Full Scale

*Invert MSB with external inverter to obtain CTC Coding

Settling Time

That interval between application of a digital step input, and final entry of the analog output within a specified window about the settled value. Harris Semiconductor usually specifies a unipolar 10V full scale step, to be measured from 10% of the input digital transition, and a window of $\pm 1/2$ LSB about the final value. The device output is then rated according to the worst (longest settling) case: low to high, or high to low. In a 12 bit system $\pm 1/2$ LSB = $\pm 0.012\%$ of FSR.

Thermal Drift

Thermal drift is based on measurements at +25°C, +125°C (T_H) and -55°C (T_L). Drift calculations are made for the high (+125°C, +25°C) and low (+25°C, -55°C) ranges, and the larger of the two values is given as a specification representing worstcase drift.

Gain Drift, Offset Drift, Reference Drift and Total Bipolar Drift are calculated in parts per million per °C as follows:

$$\text{Gain Drift} = \frac{\Delta \text{FSR}/\Delta^\circ\text{C}}{\text{FSR}} \times 10^6$$

$$\text{Offset Drift} = \frac{\Delta \text{Offset}/\Delta^\circ\text{C}}{\text{FSR}} \times 10^6$$

$$\text{Reference Drift} = \frac{\Delta V_{\text{REF}}/\Delta^\circ\text{C}}{V_{\text{REF}}} \times 10^6$$

$$\text{Total Bipolar Drift} = \frac{\Delta V_O/\Delta^\circ\text{C}}{\text{FSR}} \times 10^6$$

NOTE: FSR = Full Scale Output Voltage
- Zero Scale Output Voltage

$$\Delta \text{FSR} = \text{FSR} (+125^\circ\text{C}) - \text{FSR} (+25^\circ\text{C})$$

$$\text{or } \text{FSR} (+25^\circ\text{C}) - \text{FSR} (-55^\circ\text{C})$$

V_O = Steady-state response to any input code.

Total Bipolar Drift is the variation of output voltage with temperature, in the bipolar mode of operation. It represents the net effect of drift in Gain, Offset, Linearity and Reference Voltage. Total Bipolar Drift values are calculated, based on measurements as explained above. Gain and Offset need not be calibrated to zero at +25°C. The specified limits for TBD apply for any input code.

Accuracy

LINEARITY ERROR—(Short for "Integral Linearity Error." Also, sometimes called "Integral Nonlinearity" and "Non-linearity".) - The maximum deviation of the actual transfer characteristic from an ideal straight line. The ideal line is positioned according to end-point linearity for D/A converter products from Harris Semiconductor, i.e. the line is drawn between the end-points of the actual transfer characteristic (codes 00...0 and 11...1).

DIFFERENTIAL LINEARITY ERROR—The difference between one LSB and the output voltage change corresponding to any two consecutive codes. A Differential Nonlinearity of ± 1 LSB or less guarantees monotonicity.

MONOTONICITY—The property of a D/A converter's transfer function which guarantees that the output derivative will not change sign in response to a sequence of increasing (or decreasing) input codes. That is, the only output response to a code change is to remain constant, increase for increasing code, or decrease for decreasing code.

TOTAL ERROR—The net output error resulting from all internal effects (primarily non-ideal Gain, Offset, Linearity and Reference Voltage). Gain and offset errors must be calibrated to zero at +25°C. Then the specified limits for Total Error apply for any input code and for any temperature within the specified operating range.

Power Supply Sensitivity

Power Supply Sensitivity is a measure of the change in gain and offset of the D/A converter resulting from a change in +V_{CC}, V_{DD} or -V_{EE} supplies. It is specified under DC conditions and expressed as full scale range percent of change divided by power supply percent change.

DESIGN INFORMATION (Continued)

The information contained in this section has been developed through characterization by Harris Semiconductor and is for use as application and design data only. No guarantee is implied. Pin numbers correspond to DIP package only.

$$P.S.S. = \frac{\Delta \text{ Full Scale Range} \times 100}{\text{Full Scale Range (Nominal)}} = \frac{\Delta V \times 100}{V \text{ (Nominal)}}$$

Glitch

A glitch on the output of a D/A converter is a transient spike resulting from unequal internal ON-OFF switching times. Worst case glitches usually occur at half-scale, i.e. the major carry code transition from 011...1 to 100...0 or vice versa. For example, if turn ON is greater than OFF for 011...1 to 100...0, an intermediate state of 000...0 exists, such that, the output momentarily glitches toward zero output. Matched switching times and fast switching will reduce glitches considerably. (Measured as one half the product of duration and amplitude.)

Decoupling and Grounding

For best accuracy and high frequency performance, the grounding and decoupling scheme shown in Figure 5 should be used. Decoupling capacitors should be connected close to the HI-5687V (preferably to the device pins) and should be tantalum or electrolytic bypassed with ceramic types for best high frequency noise rejection.

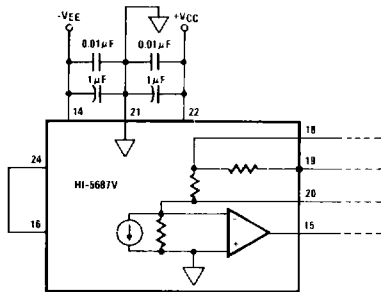


FIGURE 5.

Reference Supply

An internal 6.3 Volt reference is provided on board the HI-5687V models. This voltage reference (pin 24) must be connected to the reference input (pin 16) for specified operation. This reference may be used externally, provided current drain is limited to 2.5mA. An external buffer amplifier is recommended if this reference is to be used to drive other system components. Otherwise, variations in the load driven by the reference will result in gain variations of the HI-5687V. All gain adjustments should be made under constant load conditions.

Output Voltage Ranges

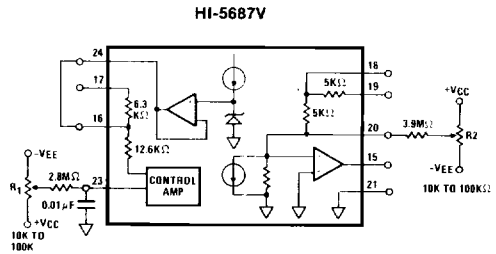


FIGURE 6.

RANGE CONNECTIONS

	RANGE	CONNECT		
		PIN 15	PIN 17	PIN 19
Unipolar	0 to +5V	18	N.C.	20
	0 to +10V	18	N.C.	N.C.
Bipolar	-2.5V	18	20	20
	-5.0V	18	20	N.C.
	-10V	19	20	15

Gain and Offset Calibration

UNIPOlar CALIBRATION	
Step 1: Offset	<ul style="list-style-type: none"> Turn all bits OFF (11...1) Adjust R₂ for zero volts out
Step 2: Gain	<ul style="list-style-type: none"> Turn all bits ON (00...0) Adjust R₁ for FS-1LSB <p>That is:</p> <p>4.9988 for 0 to +5V range 9.9976 for 0 to +10V range</p>
BIPOlar CALIBRATION	
Step 1: Offset	<ul style="list-style-type: none"> Turn all bits OFF (11...1) Adjust R₂ for Negative FS <p>That is:</p> <p>-10V for ±10V range -5V for ±5V range -2.5V for ±2.5V range</p>
Step 2: Gain	<ul style="list-style-type: none"> Turn all bits ON (00...0) Adjust R₁ for positive FS-1LSB <p>That is:</p> <p>+9.9951V for ±10V range +4.9976V for ±5V range +2.4988V for ±2.5V range</p>
This Bipolar procedure adjusts the output range end points. The maximum error at zero (half scale) will not exceed the Linearity error. See the "Accuracy" specifications.	

6
DATA CONVERSION PRODUCTS

DESIGN INFORMATION (Continued)

The information contained in this section has been developed through characterization by Harris Semiconductor and is for use as application and design data only. No guarantee is implied.

TYPICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMP	LIMITS			UNITS
					MIN	TYP	MAX	
Output Impedance	Z_O	Closed Loop, DC	10	+25°C	—	0.05	—	Ω
Internal Reference Output Impedance	REF _{OUT}	DC	10	+25°C	—	1.5	—	Ω
Output Short Circuit to GND	I _{SC}	Pin 15 to GND, Unipolar 10V Range, All Bits ON	10, 11	+25°C	—	40	—	mA

NOTES: 10. The parameters listed in this Table are controlled via design or process parameters and are not directly tested. These parameters are characterized upon initial design release and upon design changes which would affect these characteristics.

11. Under short circuit conditions, the amplifier will current limit. The duty cycle must not exceed 2.7% to maintain an acceptable current density level.